



# PMN16XNE

20 V, N-channel Trench MOSFET

29 January 2016

Product data sheet

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- Enhanced power dissipation capability of 1400 mW
- ElectroStatic Discharge (ESD) protection > 1 kV HBM

## 3. Applications

- LED driver
- Power management
- Low-side loadswitch
- Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_J = 25\text{ °C}$	-	-	20	V
$V_{GS}$	gate-source voltage		-12	-	12	V
$I_D$	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ °C}; t \leq 5\text{ s}$	[1]	-	9.1	A
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 6.9\text{ A}; T_J = 25\text{ °C}$	-	15	19	m $\Omega$

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

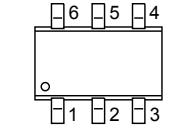
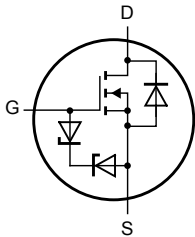


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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	 <p>TSOP6 (SOT457)</p>	 <p>017aaa255</p>
2	D	drain		
3	G	gate		
4	S	source		
5	D	drain		
6	D	drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMN16XNE	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PMN16XNE	G7

## 8. Limiting values

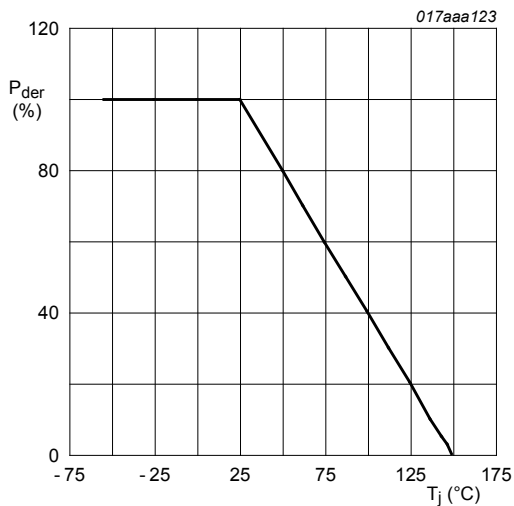
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	20	V
V <sub>GS</sub>	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	9.1	A
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	6.9	A
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	4.4	A
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs		-	28	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	550	mW
			[1]	-	1.4	W
		T <sub>sp</sub> = 25 °C		-	6.25	W
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
<b>Source-drain diode</b>						
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	1.3	A

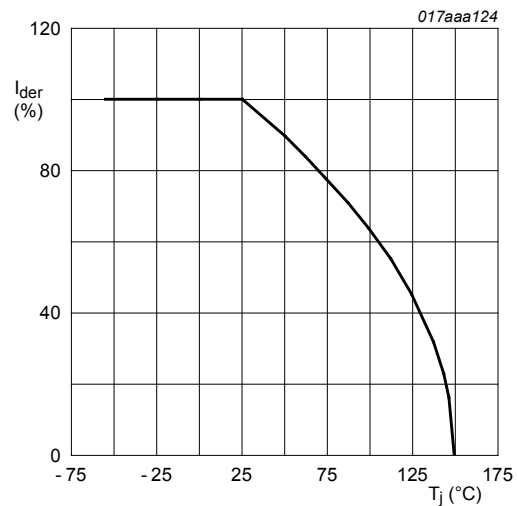
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



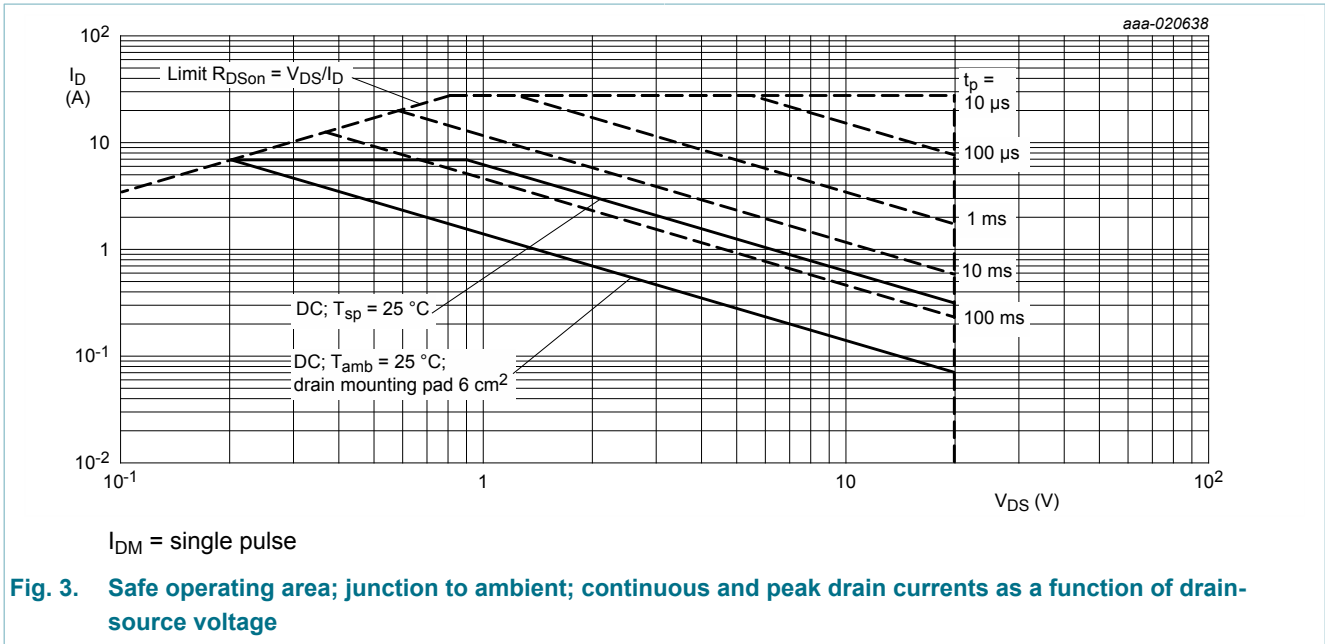
**Fig. 1. Normalized total power dissipation as a function of junction temperature**

$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100 \%$$



**Fig. 2. Normalized continuous drain current as a function of junction temperature**

$$I_{der} = \frac{I_D}{I_{D(25^\circ\text{C})}} \times 100 \%$$



## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	195	225	K/W
			[2]	-	78	90	K/W
		in free air; $t \leq 5$ s	[2]	-	45	52	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	15	20	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

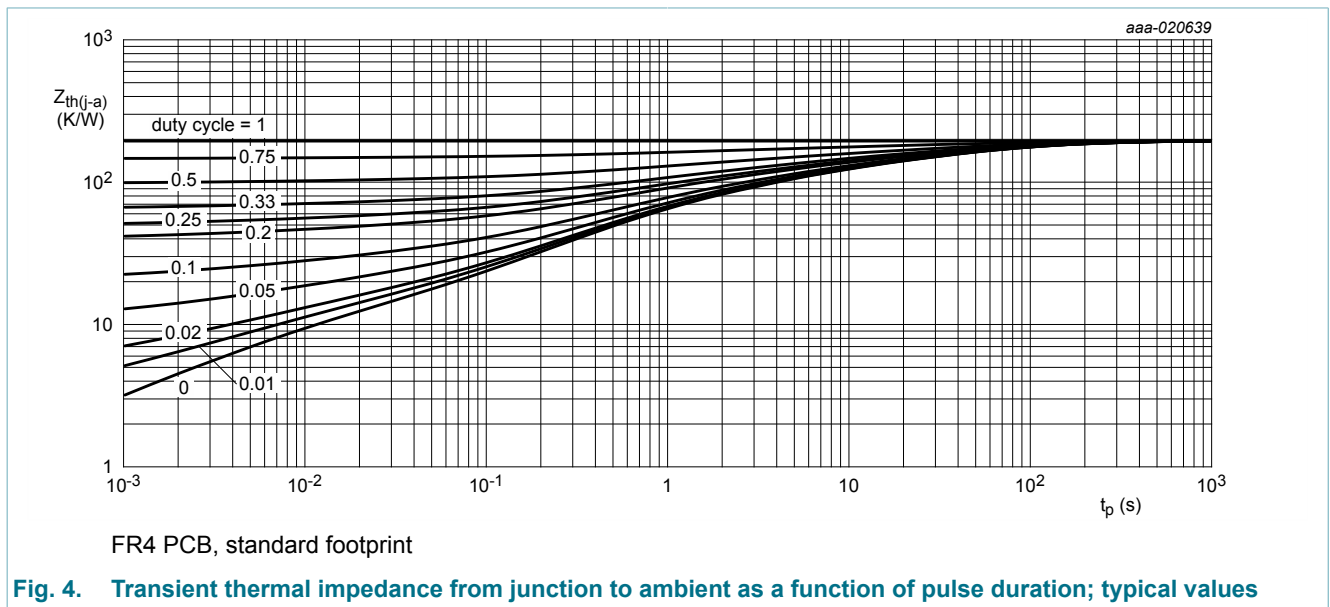
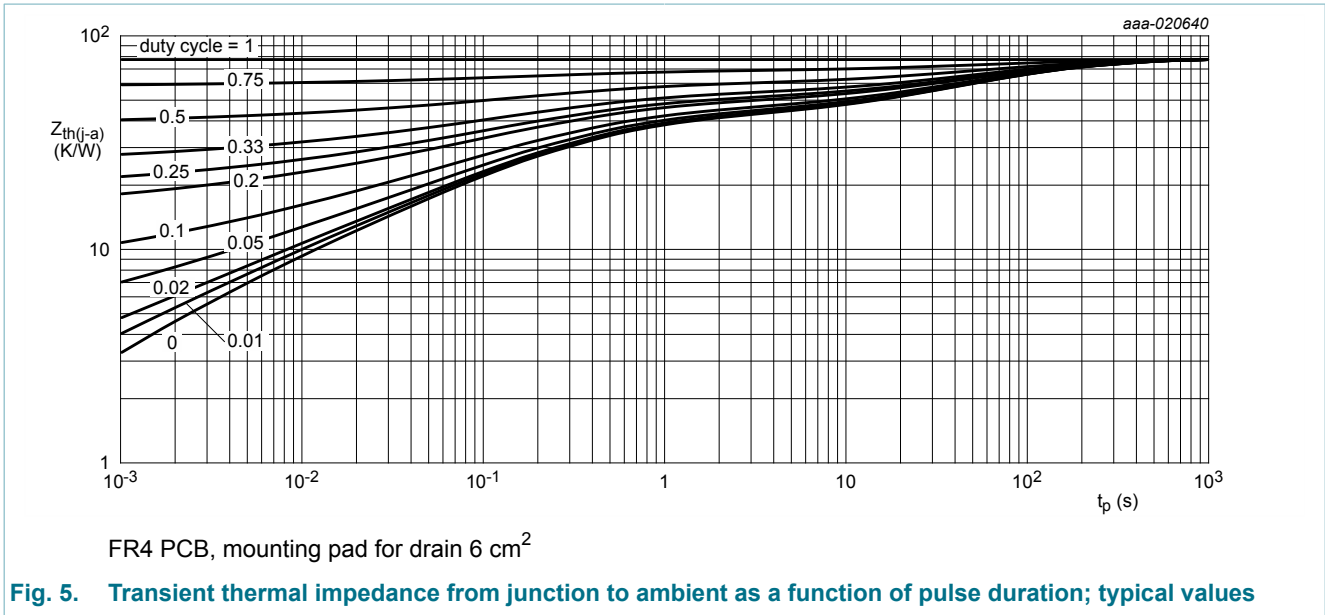


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	0.4	0.65	0.9	V
$I_{DSS}$	drain leakage current	$V_{DS} = 20 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	1	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 8 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	10	$\mu A$
		$V_{GS} = -8 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-10	$\mu A$
		$V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	2	$\mu A$
		$V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-2	$\mu A$
		$V_{GS} = 2.5 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -2.5 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 4.5 V; I_D = 6.9 A; T_j = 25 \text{ }^\circ C$	-	15	19	m $\Omega$
		$V_{GS} = 4.5 V; I_D = 6.9 A; T_j = 150 \text{ }^\circ C$	-	23	29	m $\Omega$
		$V_{GS} = 2.5 V; I_D = 6.2 A; T_j = 25 \text{ }^\circ C$	-	19	24	m $\Omega$
		$V_{GS} = 1.8 V; I_D = 1.9 A; T_j = 25 \text{ }^\circ C$	-	22	30	m $\Omega$
		$V_{GS} = 1.5 V; I_D = 0.1 A; T_j = 25 \text{ }^\circ C$	-	30	70	m $\Omega$
$g_{fs}$	forward transconductance	$V_{DS} = 10 V; I_D = 2 A; T_j = 25 \text{ }^\circ C$	-	13	-	S
$R_G$	gate resistance	$f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$	-	2.4	-	$\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 10 V; I_D = 6 A; V_{GS} = 4.5 V; T_j = 25 \text{ }^\circ C$	-	12	17	nC
$Q_{GS}$	gate-source charge		-	1.4	-	nC
$Q_{GD}$	gate-drain charge		-	2.2	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 10 V; f = 1 \text{ MHz}; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	1136	-	pF
$C_{oss}$	output capacitance		-	137	-	pF
$C_{rss}$	reverse transfer capacitance		-	112	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 10 V; I_D = 6 A; V_{GS} = 4.5 V; R_{G(ext)} = 6 \Omega; T_j = 25 \text{ }^\circ C$	-	9	-	ns
$t_r$	rise time		-	20	-	ns
$t_{d(off)}$	turn-off delay time		-	31	-	ns
$t_f$	fall time		-	32	-	ns

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 1.3 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.7	1.2	V

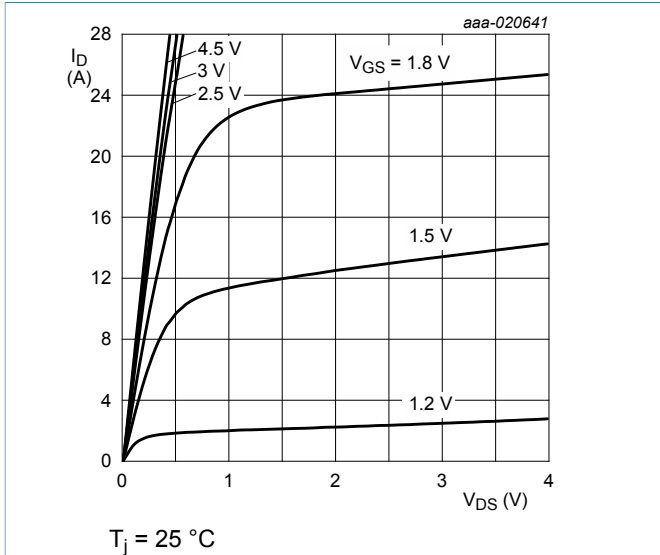


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

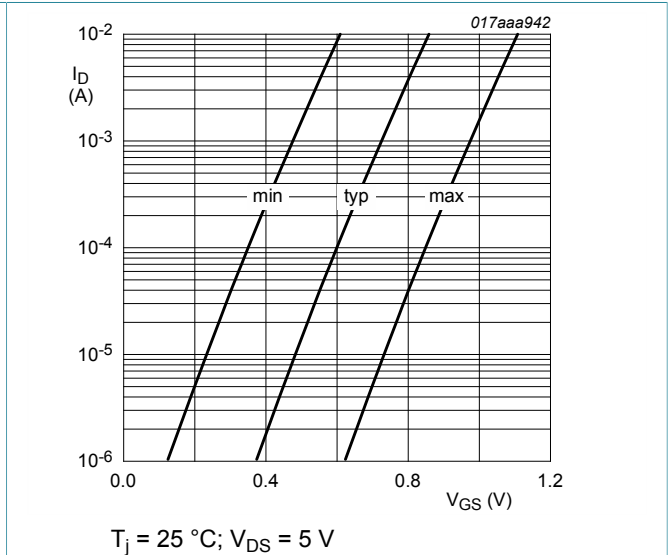


Fig. 7. Subthreshold drain current as a function of gate-source voltage

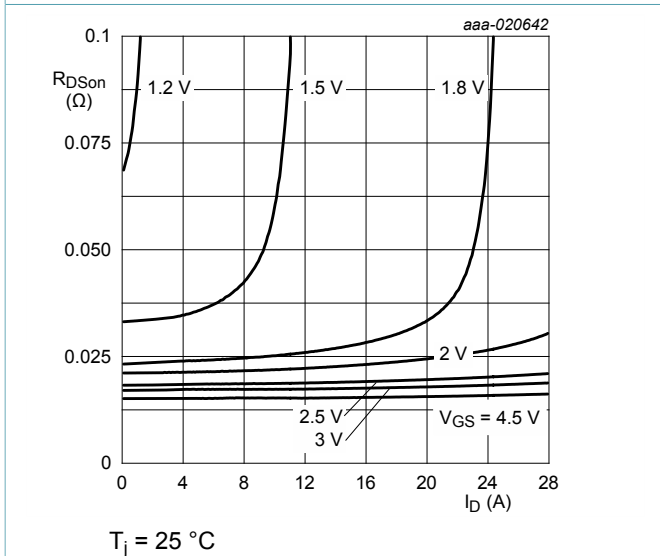


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

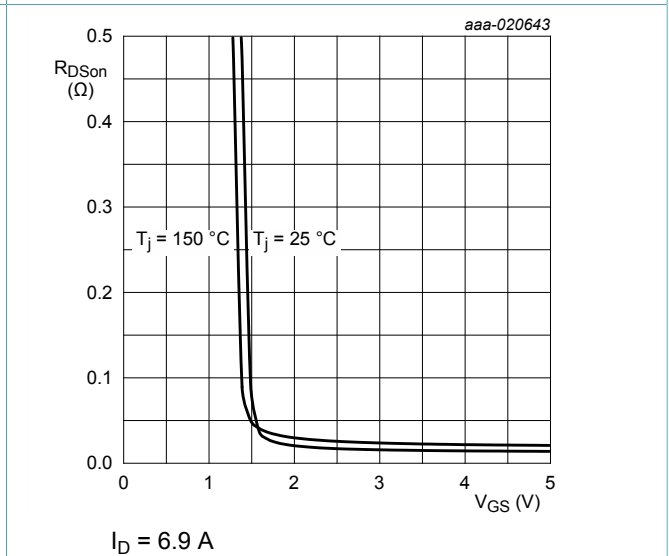
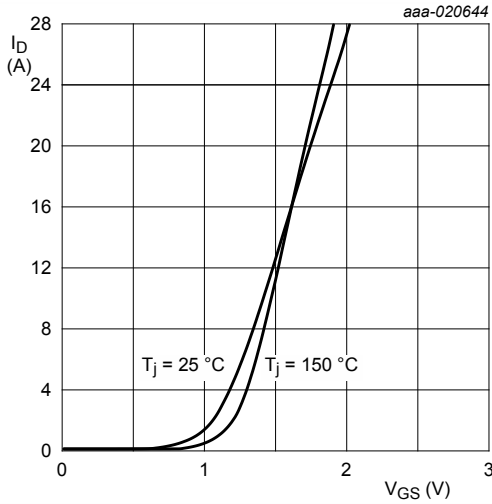
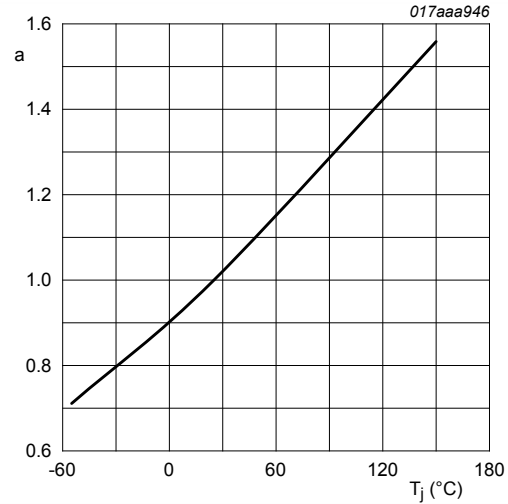


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



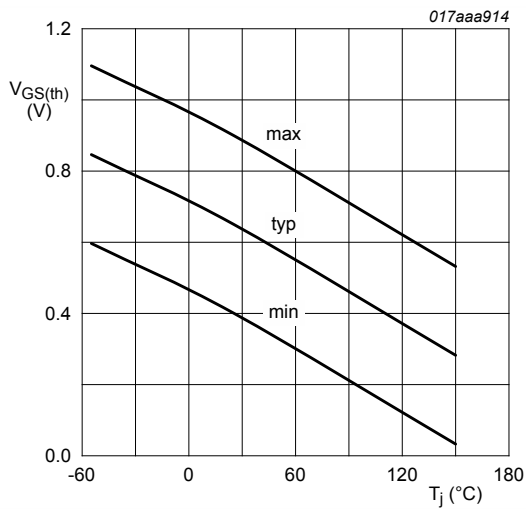


**Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



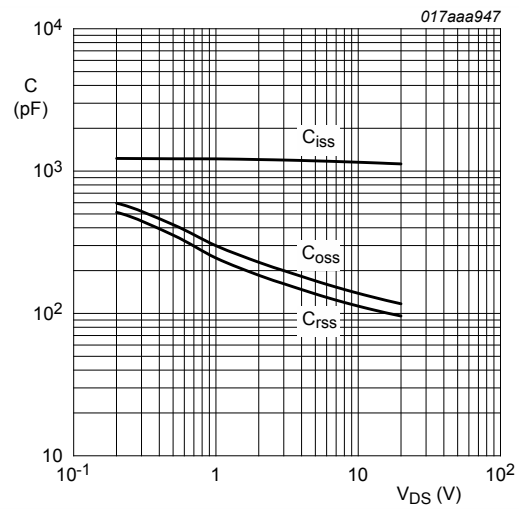
**Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values**

$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}C)}$$



**Fig. 12. Gate-source threshold voltage as a function of junction temperature**

$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$



**Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**

$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$

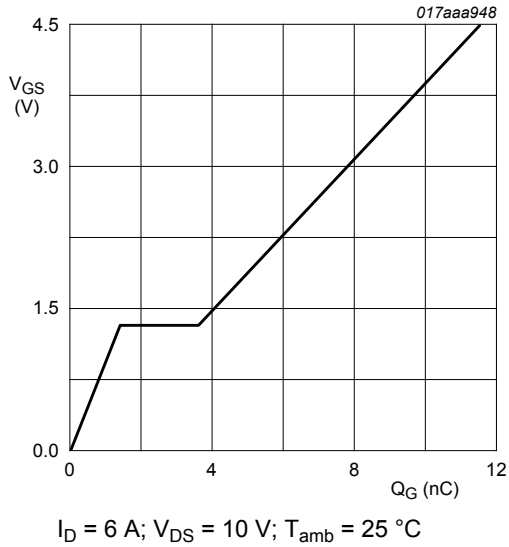


Fig. 14. Gate-source voltage as a function of gate charge; typical values

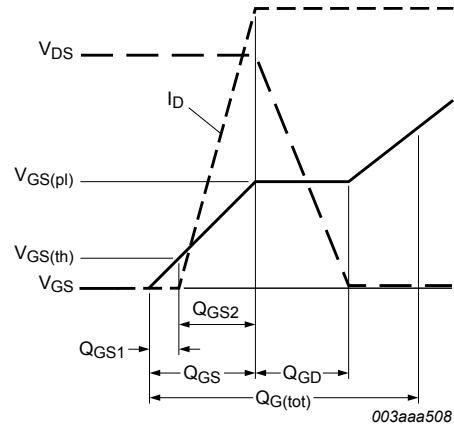


Fig. 15. MOSFET transistor: Gate charge waveform definitions

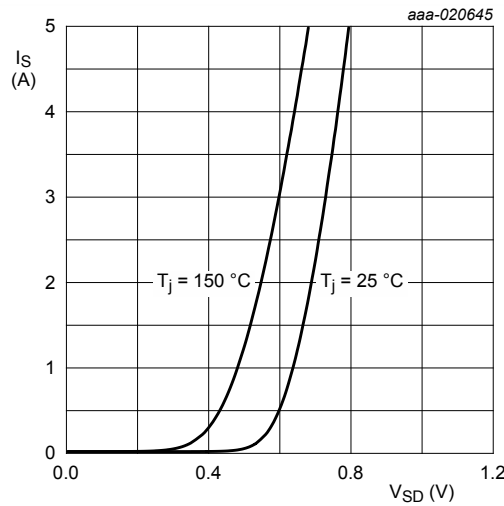


Fig. 16. Source current as a function of source-drain voltage; typical values

### 11. Test information

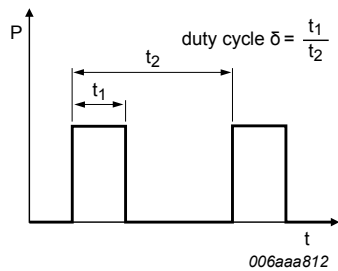


Fig. 17. Duty cycle definition

### 12. Package outline

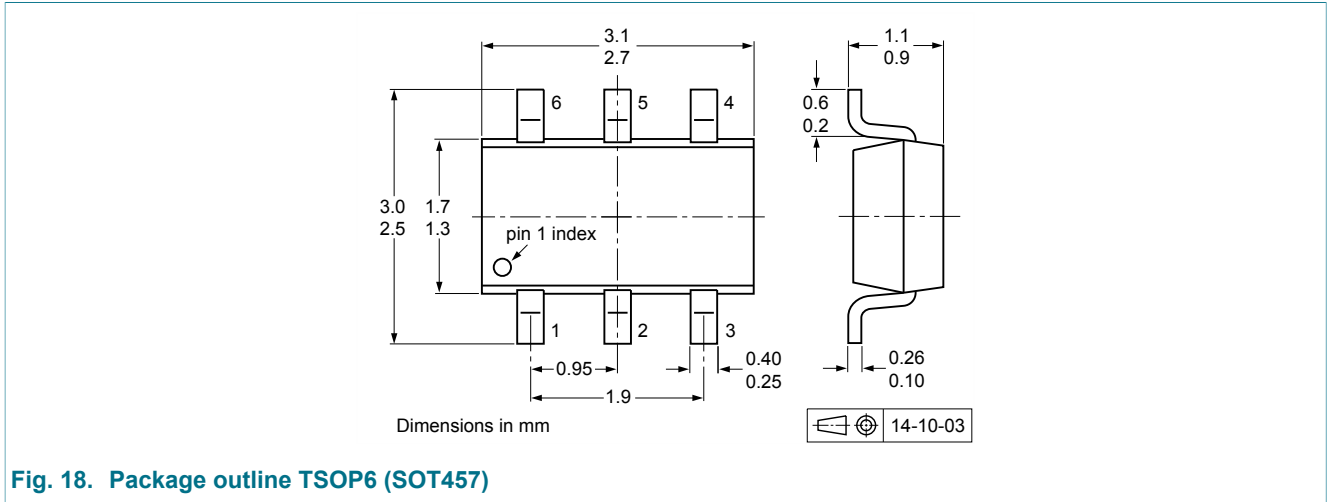


Fig. 18. Package outline TSOP6 (SOT457)

### 13. Soldering

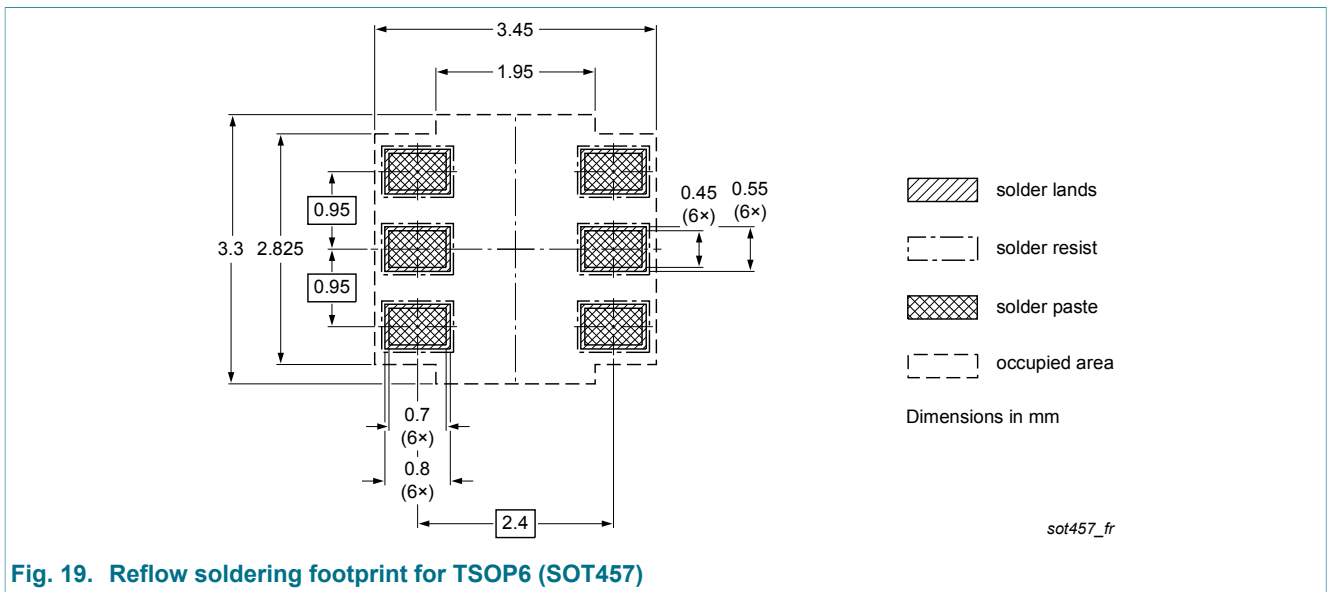


Fig. 19. Reflow soldering footprint for TSOP6 (SOT457)

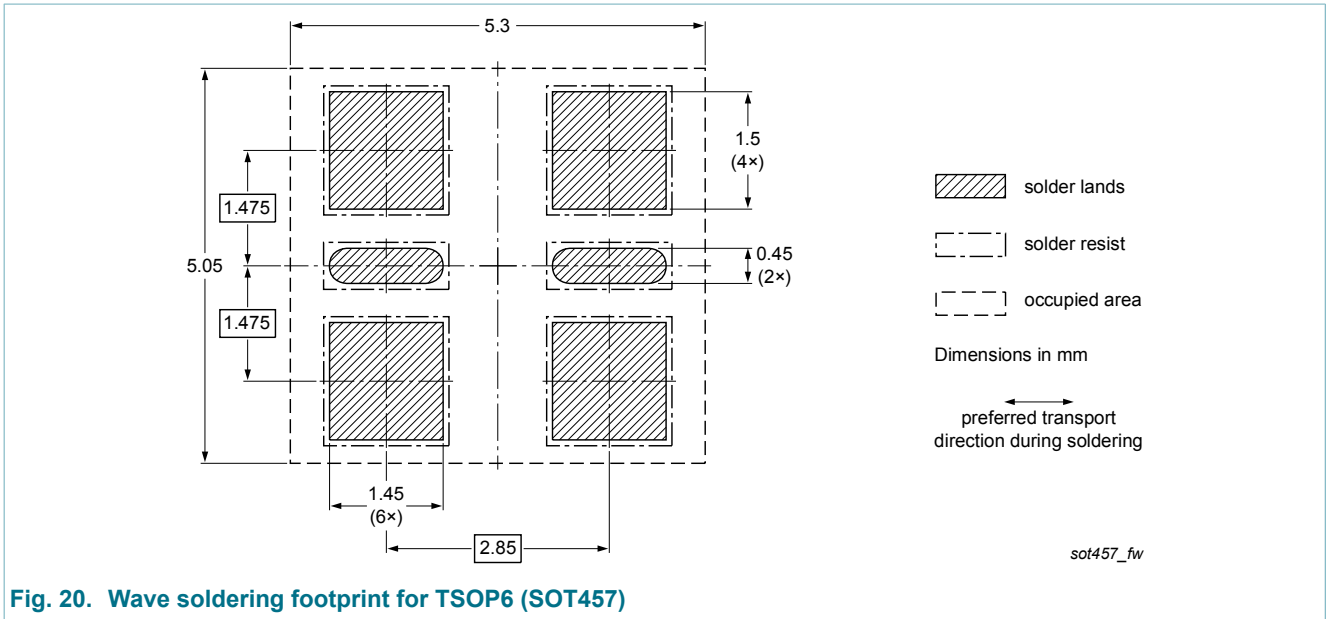


Fig. 20. Wave soldering footprint for TSOP6 (SOT457)

## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN16XNE v.1	20160129	Product data sheet	-	-

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Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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